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Form 1449*	Atty. Docket No.: 303.776US1	TECH CENTER 2000 Serial No. 09/945,495
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Fernando Gonzalez	
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U.S. PATENT DOCUMENTS

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OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner Initial	
Q40	Chang, C., et al., "Enabling Shallow Trench isolation for .01 micrometer Technologies and Beyond", <u>Symposium on VLSI Technology Digest of Technical Papers</u> , pp. 161-162, (1999)
Q40	Goebel, B., et al., "Vertical N-Channel MOSFETs for Extremely High Density Memories: The Impact of Interface Orientation on Device Performance", <u>IEEE Transactions on Electron Devices</u> , 48(5), pp. 897-906, (May 2001)
Q40	Matsuda, S., et al., "Novel Corner Rounding Process for Shallow Trench Isolation utilizing MSTs (Micro-Structure Transformation of Silicon)", <u>IEDM</u> , pp. 137-140, (1998)
Q40	Uh, H., et al., "A Strategy for Long Data Retention Time of 512Mb DRAM with 0.12micrometer Design Rule", <u>Symposium on VLSI Technology Digests of Technical Papers</u> , 2 pages, (2001)

Examiner Douglas H. Owen Date Considered 5/15/03

\*Substitute Disclosure Statement Form (PTO-1449)

\*\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.